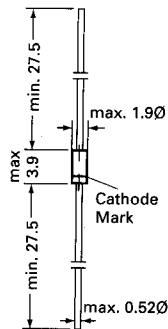


# SILICON EPITAXIAL PLANAR DIODE

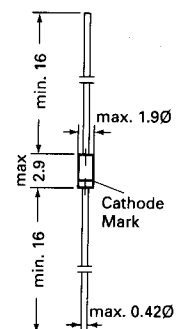
**Silicon Epitaxial Planar Diode**  
for general purpose and switching.

The types 1N4149, 1N4447 and 1N4449 are also available in glass case DO-34.



Glass case JEDEC DO-35

Dimensions in mm



Glass case JEDEC DO-34

Dimensions in mm

branded on reel  
or AMMOPAK

| Type                 | Peak reverse voltage<br>$V_{RM}$ V | Max. aver. rectified current<br>$I_o$ mA | Max. power dissip. at 25 °C<br>$P_{tot}$ mW | Max. junction temperature<br>$T_j$ °C | Max. forward voltage drop |             | Max. reverse current |            | Max. reverse recovery time |  |
|----------------------|------------------------------------|--|---|---------------------------------------|---------------------------|-------------|----------------------|------------|----------------------------|--|
|                      |                                    |  |   |                                       | $V_F$ V                   | at $I_F$ mA | $I_R$ nA             | at $V_R$ V | $t_{rr}$ ns                | Conditions   |
| 1N914                | 100                                | 75                                       | 500   | 200                                   | 1.0                       | 10          | 25                   | 20         | max. 4.0                   | $I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA |
| 1N4149 <sup>1)</sup> | 100                                | 150                                      | 500   | 200                                   | 1.0                       | 10          | 25                   | 20         | max. 4.0                   | $I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA |
| 1N4150               | 50                                 | 200                                      | 500   | 200                                   | 1.0                       | 200         | 100                  | 50         | max. 4.0                   | $I_F = I_R = 10$ to 200 mA, to $0.1 I_F$                         |
| 1N4151               | 75                                 | 150                                      | 500   | 200                                   | 1.0                       | 50          | 50                   | 50         | max. 2.0                   | $I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA |
| 1N4152               | 40                                 | 150                                      | 400   | 175                                   | 0.55                      | 0.10        | 50                   | 30         | max. 2.0                   | $I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA |
| 1N4153               | 75                                 | 150                                      | 400   | 175                                   | 0.55                      | 0.10        | 50                   | 50         | max. 2.0                   | $I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA |
| 1N4154               | 35                                 | 150 <sup>2)</sup>                        | 500   | 200                                   | 1.0                       | 30          | 100                  | 25         | max. 2.0                   | $I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA |
| 1N4447 <sup>1)</sup> | 100                                | 150                                      | 500   | 200                                   | 1.0                       | 20          | 25                   | 20         | max. 4.0                   | $I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA |
| 1N4449 <sup>1)</sup> | 100                                | 150                                      | 500   | 200                                   | 1.0                       | 30          | 25                   | 20         | max. 4.0                   | $I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA |
| 1N4450               | 40                                 | 150                                      | 400   | 175                                   | 0.54                      | 0.50        | 50                   | 30         | max. 4.0                   | $I_F = I_R = 10$ mA, to $I_R = 1$ mA                             |
| 1N4451               | 40                                 | 150                                      | 400   | 175                                   | 0.50                      | 0.10        | 50                   | 30         | max. 10                    | $I_F = I_R = 10$ mA, to $I_R = 1$ mA                             |
| 1N4453               | 30                                 | 150                                      | 400   | 175                                   | 0.55                      | 0.01        | 50                   | 20         | -                          | -  |
| 1N4454               | 75                                 | 150                                      | 400   | 175                                   | 1.0                       | 10          | 100                  | 50         | max. 4.0                   | $I_F = I_R = 10$ mA, to $I_R = 1$ mA                             |

<sup>1)</sup> These diodes are also available in glass case DO-34.

<sup>2)</sup> Valid provided that leads at a distance of 8mm from case are kept at ambient temperature.

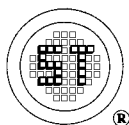
Parameters for diodes in case DO-34:

$$P_{tot} = 300 \text{ mW}$$

$$T_j = 175 \text{ °C}$$

$$T_s = -65 \text{ to } +175 \text{ °C}$$

$$R_{thA} = \leq 0.4 \text{ K/mW}$$



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